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SEP 02 2008

Shunichi SATO, reissue appl'n S.N. 10/603,418
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wherein a horizontal type MOCVD apparatus is used to carry out said MOCVD method.

65. (previously presented) The method according to claim 64, wherein the specified conditions comprise forming said alloy semiconductor at a pressure of at least that of conventional low pressure MOCVD.

66. (previously presented) The method according to claim 64, wherein said semiconductor substrate comprises GaAs.

67. (previously presented) The method according to claim 64, wherein said nitrogen containing organic compound is selected from the group consisting of dimethylhydrazine and tertiary butyl amine.

68. (previously presented) The method according to claim 64, further comprising controlling conductive properties of, and carrier concentrations in said alloy semiconductor by adding a dopant, wherein said dopant is selected from the group consisting of beryllium, magnesium, zinc, carbon, silicon, germanium, tin, sulfur, tellurium, and selenium.

Claim 69 (canceled).